

**CMR ENGINEERING COLLEGE: : HYDERABAD  
UGC AUTONOMOUS**

**I–M.TECH–I–Semester End Examinations (Regular) - February- 2026**

**DEVICE MODELING  
(VLSI SD)**

**[Time: 3 Hours]**

**[Max. Marks: 60]**

**Note:** This question paper contains two parts A and B.

Part A is compulsory which carries 10 marks. Answer all questions in Part A.

Part B consists of 5 Units. Answer any one full question from each unit. Each question carries 10 marks and may have a, b, c as sub questions.

**PART-A**

**(10 Marks)**

1. a) Define scaling and list its benefits. [2M]
- b) Define narrow-width effect. [2M]
- c) Outline What is mobility degradation? [2M]
- d) Define hot-carrier degradation. [2M]
- e) Demonstrate any two threshold voltage extraction methods. [2M]

**PART-B**

**(50 Marks)**

2. Explain the impact of scaling effects on device performance in modern VLSI design. [10M]

**OR**

- 3.a) Illustrate parasitic capacitances in MOSFET. [5M]
- b) Analyze modern multi-gate MOSFET structures. [5M]

- 4.a) Derive flat-band voltage and threshold voltage expressions. [5M]
- b) Interpret and analyze high-frequency and low-frequency C–V characteristics. [5M]

**OR**

- 5.a) Examine DIBL and channel length modulation. [5M]
- b) Explain the short channel effects and its influence on device characteristics like threshold voltage and temperature. [5M]

6. Explain and assess temperature effects on MOSFET current characteristics. [10M]

**OR**

- 7.a) Construct the Meyer capacitance model and small-signal equivalent circuit. [5M]
- b) Analyze sub-threshold slope and leakage mechanisms. [5M]

- 8.a) Explain and evaluate hot-carrier effects and interface trap generation. ([5M]
- b) Describe SPICE parameter extraction and model calibration techniques. [5M]

**OR**

- 9.a) Analyze gate oxide reliability concerns. [5M]
- b) Demonstrate MOSFET simulation using SPICE parameters. [5M]

10. Explain and analyze mobility and threshold voltage extraction methods. [10M]

**OR**

- 11.a) Discuss worst-case corner modeling approaches. [5M]
- b) Assess yield estimation techniques in VLSI design. [5M]

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